



产品数据手册 Product Datasheet 版本 Ver 21.10

TIM250PHM33-PSA011

半桥型 IGBT 模块 Half Bridge IGBT

关键参数		Key Parameters	
V_{CES}		3300	V
$V_{CE(sat)}$	Typ.	2.5	V
I_C	Max.	250	A
$I_{C(RM)}$	Max.	500	A

典型应用		Typical Applications	
● 牵引辅变		Traction Auxiliaries	
● 电机控制		Motor Controllers	
● 斩波		Choppers	
● 高可靠性逆变器		High Reliability Inverter	

特点		Features	
● AISiC 基板		AISiC Baseplate	
● AIN 衬板		AIN Substrates	
● 高热循环能力		High Thermal Cycling Capability	
● 10μs 短路承受能力		10μs Short Circuit Withstand	

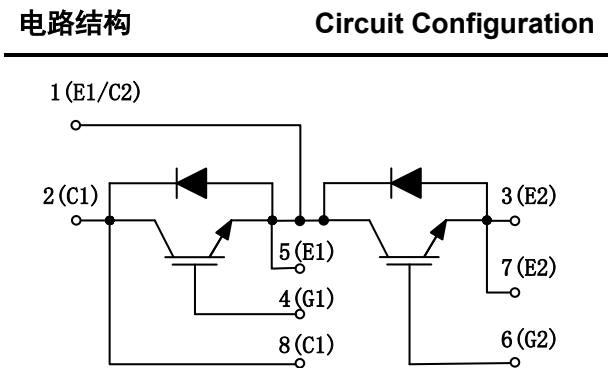


图 1. 电路结构
Fig. 1 Circuit configuration

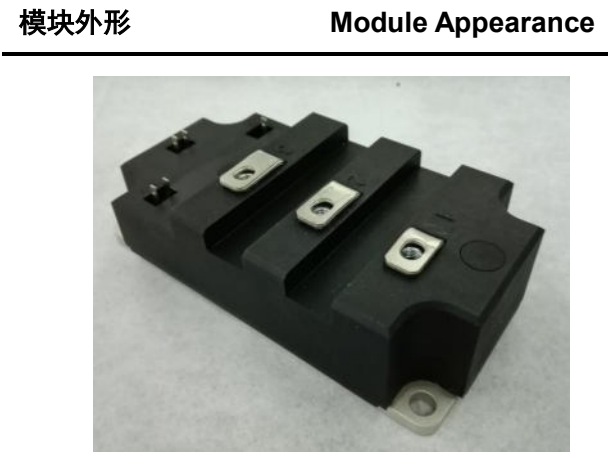


图 2. 模块外形
Fig. 2 Module appearance

模块标签说明		Module Label Code Instruction	
	数据位置 Data position	数据内容 Content of data	
	1—8	模块批次号 Module batch number	
	9—12	模块序列号 Module serial number	

最大额定值
Absolute Maximum Ratings

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
V_{CES}	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^{\circ}\text{C}$	3300	V
V_{GES}	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^{\circ}\text{C}$	± 20	V
I_C	集电极电流 Collector-emitter current	$T_C = 100\text{ }^{\circ}\text{C}$	250	A
$I_{C(PK)}$	集电极峰值电流 Peak collector current	$t_P = 1\text{ms}$	500	A
P_{max}	晶体管部分最大损耗 Max. transistor power dissipation	$T_{vj} = 150\text{ }^{\circ}\text{C}, T_C = 25\text{ }^{\circ}\text{C}$	2.6	kW
t_t	二极管 t_t 值 Diode t_t	$V_R = 0V, t_P = 10\text{ms}, T_{vj} = 150\text{ }^{\circ}\text{C}$	20	kA^2s
V_{isol}	绝缘电压(模块) Isolation voltage – per module	短接所有端子，端子与基板间施加电压 (Connected terminals to baseplate), AC RMS, 1 min, 50Hz, $T_C = 25\text{ }^{\circ}\text{C}$	6	kV
Q_{PD}	局部放电电荷(模块) Partial discharge – per module	IEC1287. $V_1 = 3500V, V_2 = 2600V, 50\text{Hz RMS}$	10	pC

热和机械数据
Thermal & Mechanical Data

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	33.0	mm
	端子-端子 Terminal to terminal	33.0	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	20.0	mm
	端子-端子 Terminal to terminal	20.0	mm
相对漏电起痕指数 CTI (Comparative Tracking Index)		>600	

热和机械数据

Thermal & Mechanical Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	最大值 Max.	单位 Unit
$R_{th(J-C)} IGBT$	IGBT 结壳热阻 Thermal resistance – IGBT			48	K / kW
$R_{th(J-C)} Diode$	二极管结壳热阻 Thermal resistance – Diode			80	K / kW
$R_{th(C-H)} IGBT$	接触热阻(IGBT) Thermal resistance – case to heatsink (IGBT)	安装力矩 5Nm, 导热脂 1W/m·°C Mounting torque 5Nm, with mounting grease 1W/m·°C		18	K / kW
$R_{th(C-H)} Diode$	接触热阻(Diode) Thermal resistance – case to heatsink (Diode)	安装力矩 5Nm, 导热脂 1W/m·°C Mounting torque 5Nm, with mounting grease 1W/m·°C		36	K / kW
$T_{vj op}$	工作结温 Operating junction temperature	IGBT 部分 (IGBT)	-40	150	°C
		二极管部分(Diode)	-40	150	°C
T_{stg}	存储温度 Storage temperature range		-40	150	°C
M	安装力矩 Screw torque	安装紧固用 – M6 Mounting – M6		5	Nm
		电路互连用 – M5 Electrical connections – M5		4	Nm

电特性值
Electrical Characteristics

除非特别声明，否则 $T_C = 25\text{ }^{\circ}\text{C}$
 $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{CES}	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 125\text{ }^{\circ}\text{C}$			15	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150\text{ }^{\circ}\text{C}$			25	mA
I_{GES}	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			1	μA
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 20\text{mA}, V_{GE} = V_{CE}$	5.5	6.1	7.0	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 250A$		2.50	2.80	V
		$V_{GE} = 15V, I_C = 250A, T_{vj} = 125\text{ }^{\circ}\text{C}$		3.15	3.45	V
		$V_{GE} = 15V, I_C = 250A, T_{vj} = 150\text{ }^{\circ}\text{C}$		3.30	3.60	V
I_F	二极管正向直流电流 Diode forward current	DC		250		A
I_{FRM}	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1\text{ms}$		500		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 250A, V_{GE} = 0$		2.10	2.40	V
		$I_F = 250A, V_{GE} = 0, T_{vj} = 125\text{ }^{\circ}\text{C}$		2.25	2.55	V
		$I_F = 250A, V_{GE} = 0, T_{vj} = 150\text{ }^{\circ}\text{C}$		2.25	2.55	V
I_{SC}	短路电流 Short circuit current	$T_{vj} = 150\text{ }^{\circ}\text{C}, V_{CC} = 2500V,$ $V_{GE} \leq 15V, t_p \leq 10\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 60747-9		900		A

注意: 1. (*1) 表示该参数的测试点为辅助母排端子 (*1) indicates it is measured at the auxiliary busbar terminal),

Note: 2. (*2) 表示 L 是电路杂散电感加上 L_M (*2) indicates L is the circuit stray inductance plus L_M).



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电特性值

Electrical Characteristics

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符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
C_{ies}	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		27		nF
Q_g	栅极电荷 Gate charge	$\pm 15V$		2.6		μC
C_{res}	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		0.9		nF
L_M	模块电感 Module inductance			40		nH
$R_{CC'+EE'}$	模块引线电阻, 端子-芯片 Module lead resistance, terminal-chip			0.5		m Ω

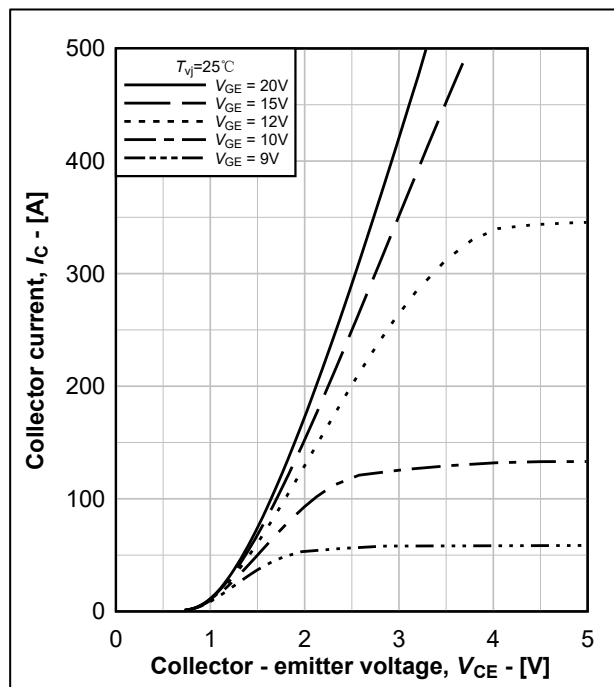
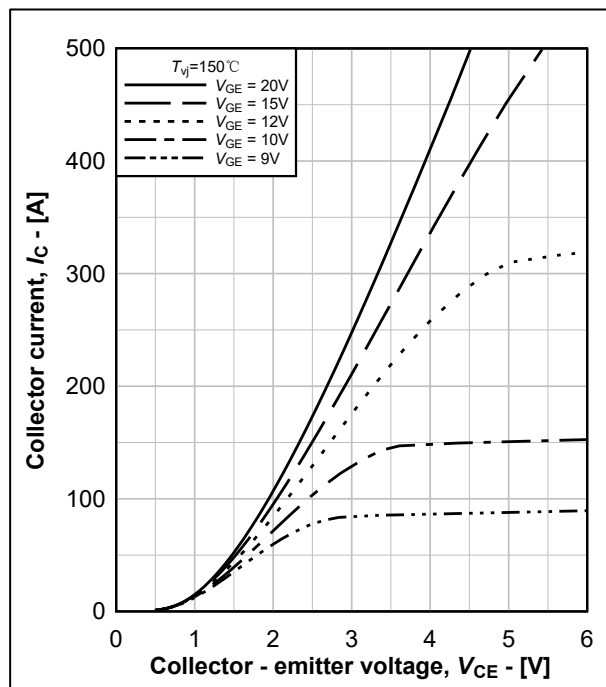
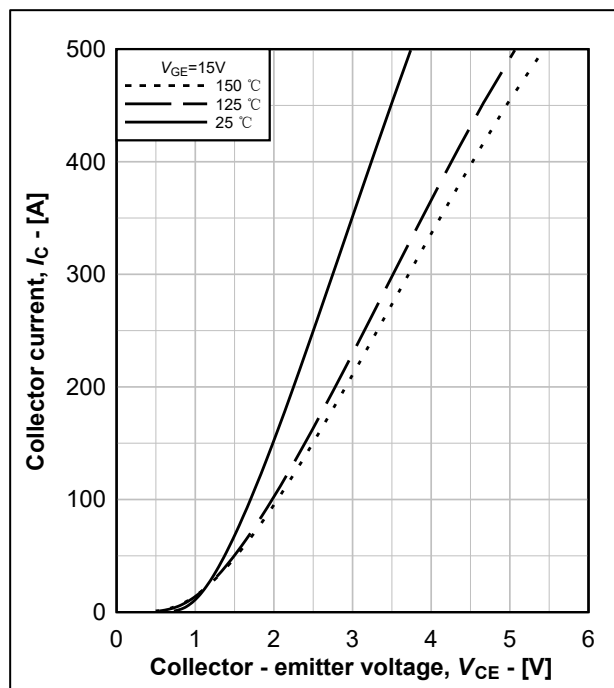
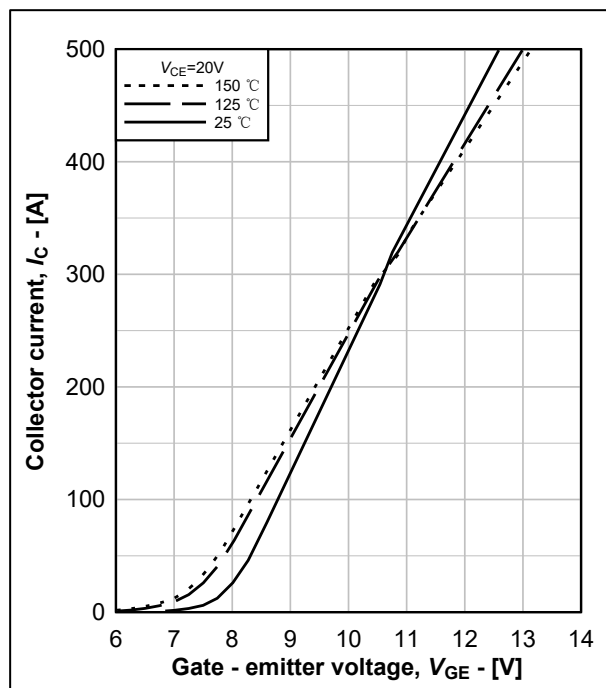
Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

注意: 该器件对静电敏感, 用户须采取 ESD 防护措施。

电特性值

Electrical Characteristics

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions		最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 250A$, $V_{CE} = 1800V$, $V_{GE} = \pm 15V$, $R_{G(Off)} = 9.0\Omega$, $C_{GE} = 56nF$, $L_S = 150nH$,	$T_{vj}= 25\text{ }^{\circ}C$		1480		ns
			$T_{vj}= 125\text{ }^{\circ}C$		1550		
			$T_{vj}= 150\text{ }^{\circ}C$		1570		
t_f	下降时间 Fall time		$T_{vj}= 25\text{ }^{\circ}C$		1280		ns
			$T_{vj}= 125\text{ }^{\circ}C$		1920		
			$T_{vj}= 150\text{ }^{\circ}C$		2120		
E_{OFF}	关断损耗 Turn-off energy loss		$T_{vj}= 25\text{ }^{\circ}C$		300		mJ
			$T_{vj}= 125\text{ }^{\circ}C$		380		
			$T_{vj}= 150\text{ }^{\circ}C$		400		
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$I_C = 250A$, $V_{CE} = 1800V$, $V_{GE} = \pm 15V$, $R_{G(On)} = 6.0\Omega$, $C_{GE} = 56nF$, $L_S = 150nH$,	$T_{vj}= 25\text{ }^{\circ}C$		640		ns
			$T_{vj}= 125\text{ }^{\circ}C$		650		
			$T_{vj}= 150\text{ }^{\circ}C$		650		
t_r	上升时间 Rise time		$T_{vj}= 25\text{ }^{\circ}C$		220		ns
			$T_{vj}= 125\text{ }^{\circ}C$		235		
			$T_{vj}= 150\text{ }^{\circ}C$		238		
E_{ON}	开通损耗 Turn-on energy loss		$T_{vj}= 25\text{ }^{\circ}C$		395		mJ
			$T_{vj}= 125\text{ }^{\circ}C$		510		
			$T_{vj}= 150\text{ }^{\circ}C$		565		
Q_{rr}	二极管反向恢复电荷 Diode reverse recovery charge	$I_F = 250A$, $V_{CE} = 1800V$, - $di_F/dt = 1200A/\mu s$, ($T_{vj}= 125\text{ }^{\circ}C$).	$T_{vj}= 25\text{ }^{\circ}C$		190		μC
			$T_{vj}= 125\text{ }^{\circ}C$		295		
			$T_{vj}= 150\text{ }^{\circ}C$		335		
I_{rr}	二极管反向恢复电流 Diode reverse recovery current		$T_{vj}= 25\text{ }^{\circ}C$		185		A
			$T_{vj}= 125\text{ }^{\circ}C$		210		
			$T_{vj}= 150\text{ }^{\circ}C$		216		
E_{rec}	二极管反向恢复损耗 Diode reverse recovery energy		$T_{vj}= 25\text{ }^{\circ}C$		223		mJ
			$T_{vj}= 125\text{ }^{\circ}C$		360		
			$T_{vj}= 150\text{ }^{\circ}C$		410		

图 3. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$ Fig.3 Typical IGBT output characteristics, $I_C = f(V_{CE})$ 图 4. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$ Fig.4 Typical IGBT output characteristics, $I_C = f(V_{CE})$ 图 5. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$ Fig.5 Typical IGBT output characteristics, $I_C = f(V_{CE})$ 图 6. IGBT 传输特性典型曲线, $I_C = f(V_{GE})$ Fig.6 Typical IGBT transfer characteristics, $I_C = f(V_{GE})$

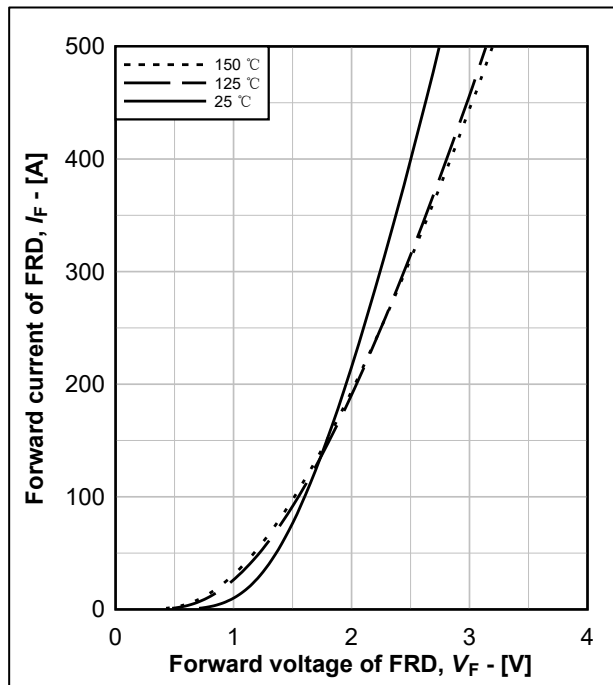

图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$

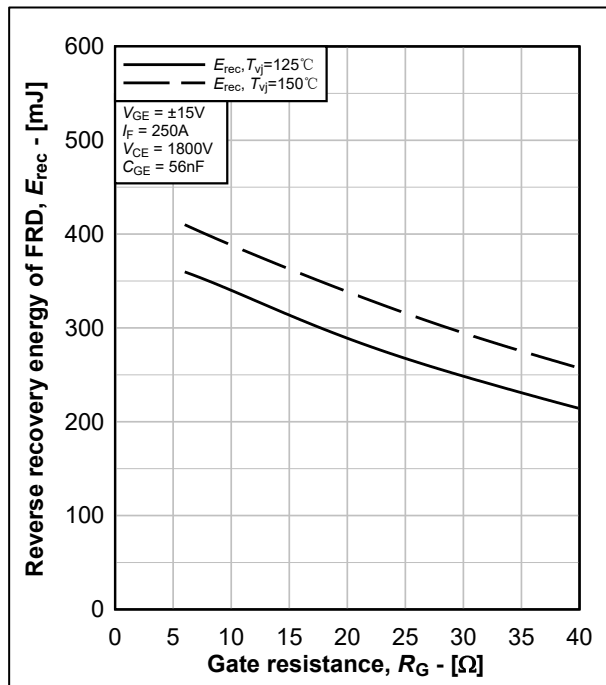
Fig.7 Typical FRD output characteristics, $I_F = f(V_F)$

图 8. FRD 反向恢复能耗典型曲线, $E_{rec} = f(R_G)$

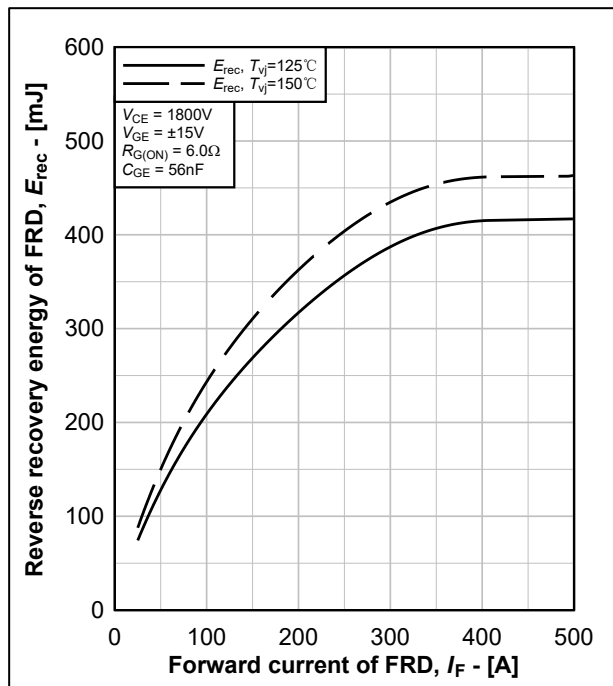
Fig.8 Typical FRD E_{rec} , $E_{rec} = f(R_G)$

图 9. FRD 反向恢复能耗典型曲线, $E_{rec} = f(I_F)$

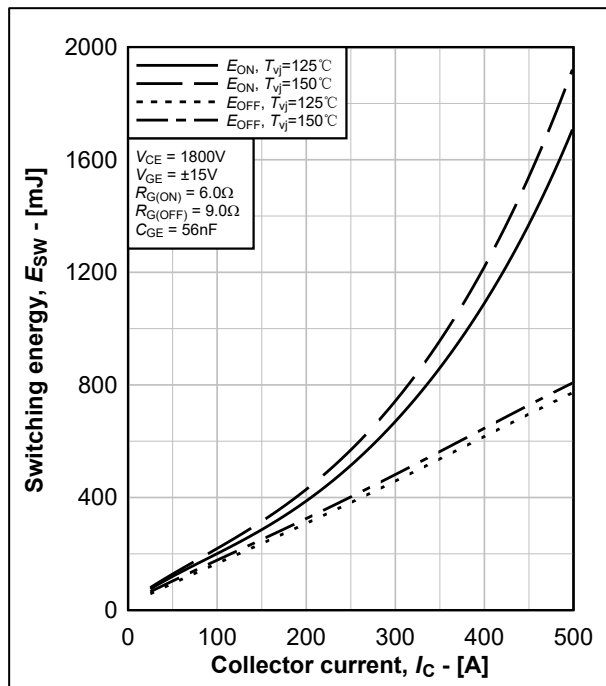
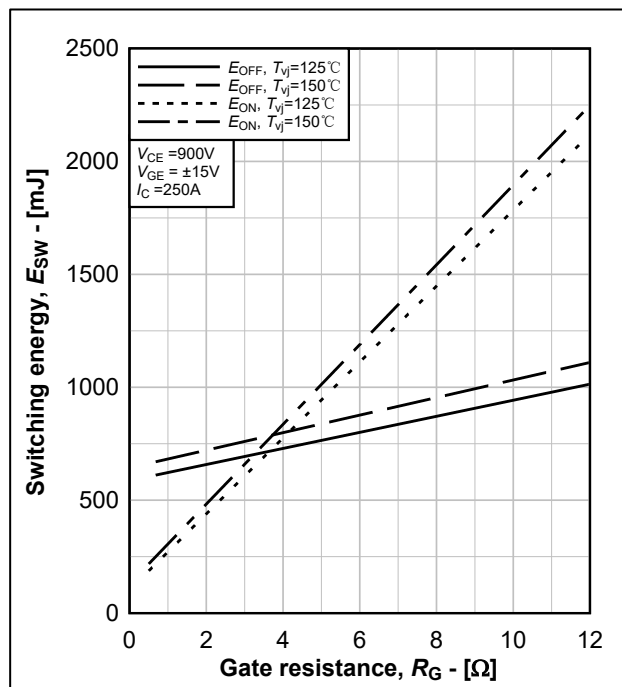
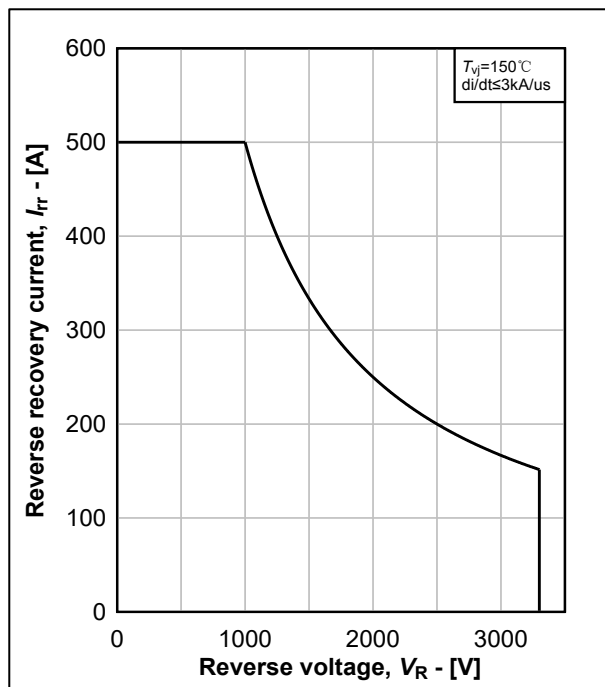
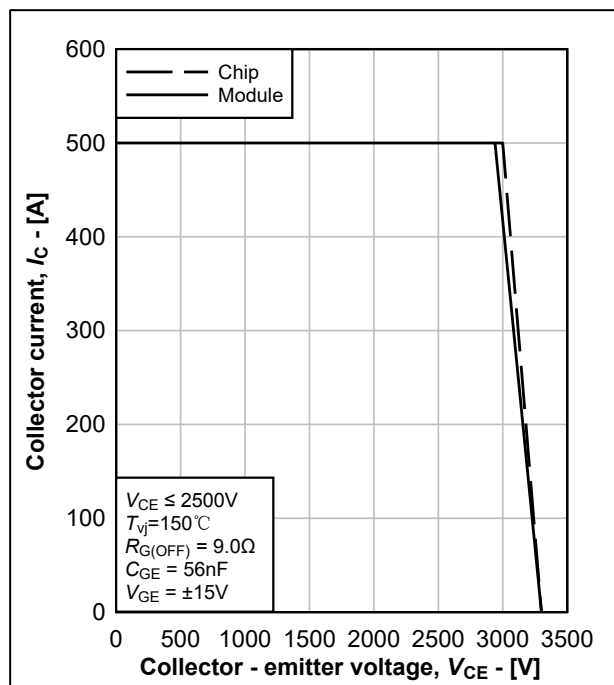
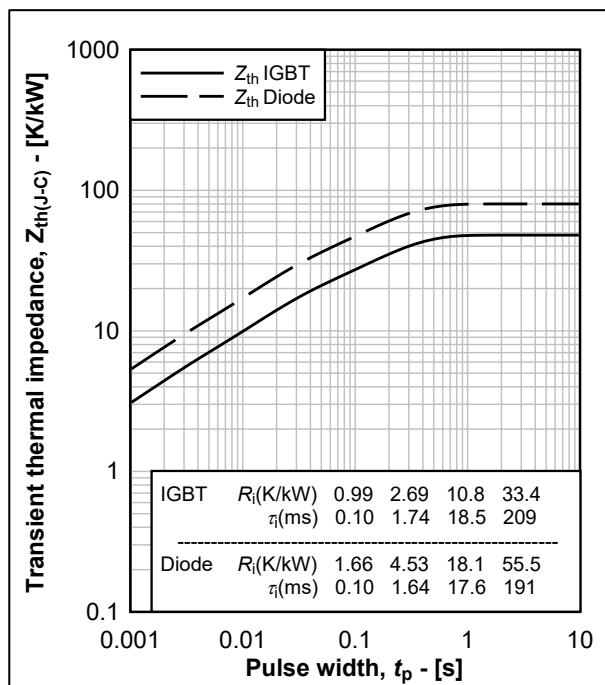
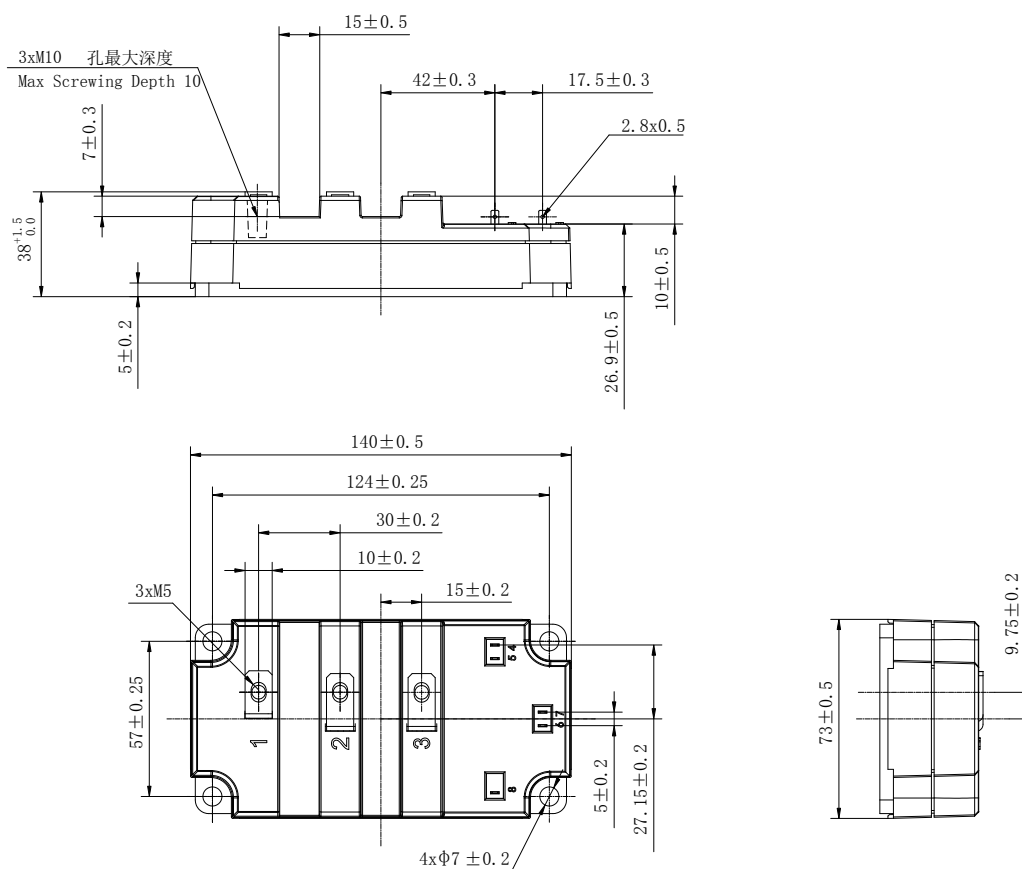
Fig.9 Typical FRD E_{rec} , $E_{rec} = f(I_F)$

图 10. IGBT 开关能耗典型曲线, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

Fig.10 Typical IGBT switching energy, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

图 11. IGBT 开关能耗典型曲线, $E_{on} = f(R_G)$, $E_{off} = f(R_G)$ Fig.11 Typical IGBT switching energy, $E_{on} = f(R_G)$, $E_{off} = f(R_G)$ 图 12. 二极管反偏安全工作区, $I_{rr} = f(V_R)$ Fig.12 Diode reverse bias safe operating area, $I_{rr} = f(V_R)$ 图 13. IGBT 反偏安全工作区, $I_C = f(V_{CE})$ Fig.13 Reverse bias safe operating area of IGBT, $I_C = f(V_{CE})$ 图 14. 瞬态热阻抗曲线, $Z_{th(j-c)} = f(t_p)$ Fig.14 Transient thermal impedance, $Z_{th(j-c)} = f(t_p)$



重量 Weight: 750g 模块外观类型 Module outline code: P

图 15 模块外观尺寸

Fig. 15 Module outlines

株洲中车时代半导体有限公司

ZHUZHOU CRRC TIMES SEMICONDUCTOR CO., LTD

地 址	Address	湖南省株洲市石峰区田心工业园	Tianxin Industrial Park, Shifeng District, ZhuZhou City, Hunan Province, China
邮 编	Zipcode	412001	
电 话	Telephone	+86 (0)731-28498268, 28498238, 28493472	
传 真	Fax	+86 (0)731-28498851, 28498494	
电子邮箱	Email	sbu@crzczic.cc	
网 址	Web Site	http://www.sbu.crrczic.cc	



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(3) If there are special requirements for the product, or apply it in special industries (such as aerospace, medical, life support, etc.), we strongly recommend that to perform joint application risk and quality assessments, get the quality agreements.

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(5) When the products are in use, it is strictly prohibited to touch. After power off, to ensure that there is no residual charge and the products have been cooled before they can be touched. And all operations must be under ESD protection measures.

(6) We annotate datasheet in the top right hand corner of the front page, to indicate product status. The annotation “Preliminary” indicates the product design is complete and final characterization for volume production is in progress, the product information in the datasheet is currently can be referenced, but some details may change in the future. There is no annotation indicates the product is capable to produce in batch quantity.